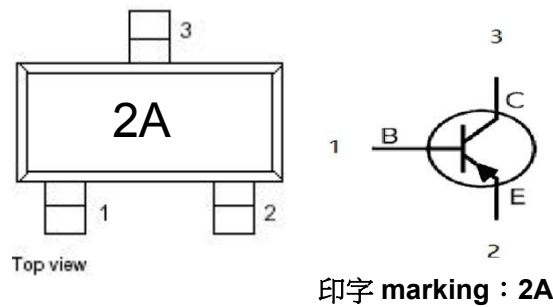


一、Features 产品特性

MAXIMUM RATINGS(T_a=25°C) 最大额定值

CHARACTERISTIC 特性参数	Symbol 符号	Rating 额定值	Unit 单位
Collector-Emitter Voltage 集电极-发射极电压	V _{CEO}	-40	Vdc
Collector-Base Voltage 集电极-基极电压	V _{CBO}	-40	Vdc
Emitter-Base Voltage 发射极-基极电压	V _{EBO}	-5	Vdc
Collector Current—Continuous 集电极电流-连续	I _C	-200	mAdc

THERMAL CHARACTERISTICS 热特性

CHARACTERISTIC 特性参数	Symbol 符号	Max 最大值	Unit 单位
Total Device Dissipation 总耗散功率 FR-5 Board(1) (T _A =25°C 环境温度=25°C)	P _D	225	mW
Derate above 25°C 超过 25°C 递减		1.8	mW/°C
Thermal Resistance Junction to Ambient 热阻	R _{JA}	556	°C/W
Total Device Dissipation Alumina Substrate,(2) T _A =25°C 总耗散功率 氧化铝衬底	P _D	300	mW
Derate above 25°C 超过 25°C 递减		2.4	mW/°C
Thermal Resistance Junction to Ambient 热阻	R _{JA}	417	°C/W
Junction and Storage Temperature 结温和储存温度	T _J , T _{stg}	150, -55 to +150	°C

ELECTRICAL CHARACTERISTICS 电特性
(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Test Condition 测试条件	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector Cutoff Current 集电极截止电流	I _{CEX}	V _{CE} =-30Vdc, V _{EB} =-3.0 Vdc	—	—	-50	nAdc
Base Cutoff Current 基极截止电流	I _{BEX}	V _{CE} =-30Vdc, V _{EB} =-3.0Vdc	—	—	-50	nAdc
Collector-Emitter Breakdown	V _{(BR)CEO}	I _C =-1.0mAdc, I _B =0	-40	—	—	Vdc

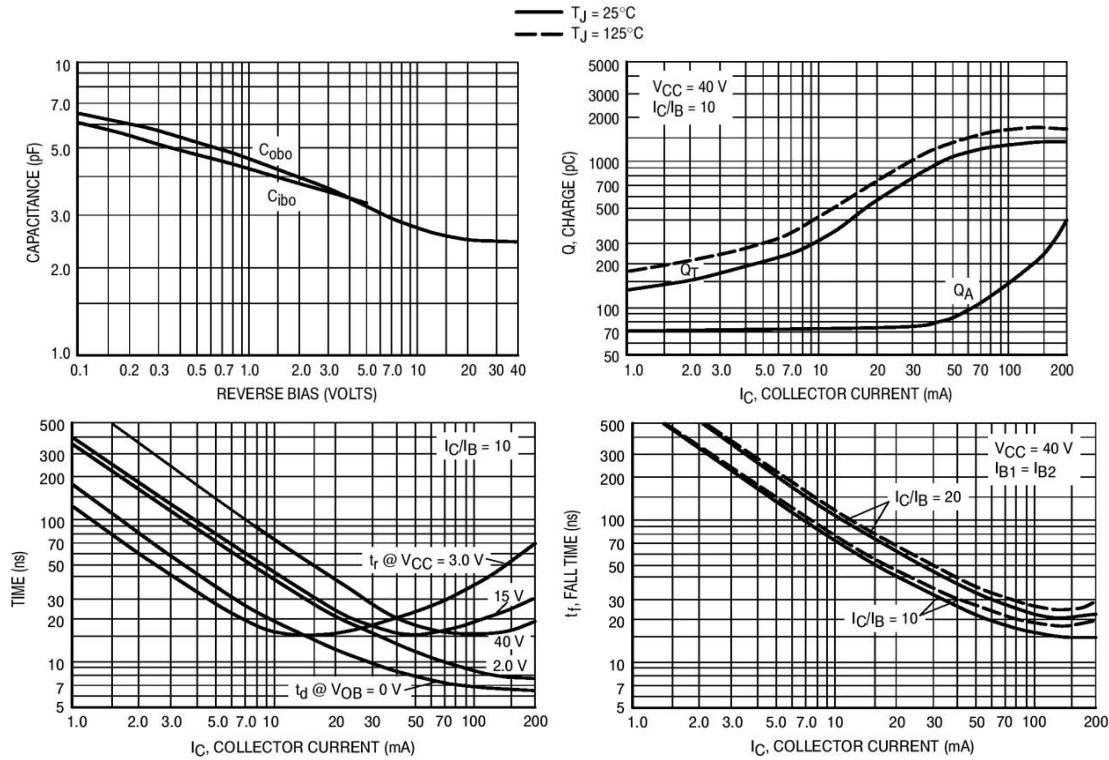
Voltage(3) 集电极-发射极击穿电压						
Collector-Base Breakdown Voltage 集电极-基极击穿电压	$V_{(BR)CBO}$	$I_C=-10\mu A_{dc}, I_E=0$	-40	—	—	Vdc
Emitter-Base Breakdown Voltage 发射极-基极击穿电压	$V_{(BR)EBO}$	$I_E=-10\mu A_{dc}, I_C=0$	-5	—	—	Vdc
DC Current Gain 直流电流增益	h_{FE}	$I_C=-0.1mA_{dc}, V_{CE}=-1.0V_{dc}$	60	—	—	—
		$I_C=-1.0mA_{dc}, V_{CE}=-1.0V_{dc}$	80	—	—	
		$I_C=-10mA_{dc}, V_{CE}=-1.0V_{dc}$	100	—	300	
		$I_C=-50mA_{dc}, V_{CE}=-1.0V_{dc}$	60	—	—	
		$I_C=-100mA_{dc}, V_{CE}=-1.0V_{dc}$	30	—	—	
Collector-Emitter Saturation Voltage(3)集电极发射极饱和压降	$V_{CE(sat)}$	$I_C=-10mA_{dc}, I_B=-1.0mA_{dc}$	—	—	-0.25	Vdc
		$I_C=-50mA_{dc}, I_B=-5.0mA_{dc}$	—	—	-0.4	
Base-Emitter Saturation Voltage 基极-发射极饱和压降	$V_{BE(sat)}$	$I_C=-10mA_{dc}, I_B=-1.0mA_{dc}$	-0.65	—	-0.85	Vdc
		$I_C=-50mA_{dc}, I_B=-5.0mA_{dc}$		—	-0.95	
Current-Gain-Bandwidth Product 电流增益-带宽乘积	f_T	$I_C=-10mA_{dc}, V_{CE}=-20V_{dc}, f=100MHz$	250	—	—	MHz
Output Capacitance 输出电容	C_{obo}	$V_{CB}=-5.0V_{dc}, I_E=0, f=1.0MHz$	—	—	4.5	pF
INput Capacitance 输入电容	C_{ibo}	$V_{EB}=-0.5V_{dc}, I_C=0, f=1.0MHz$	—	—	10	pF
Input Impedance 输入抗阻	h_{ie}	$V_{CE}=-10V_{dc}, I_C=-1.0mA_{dc}, f=1.0KHz$	1.0	—	10	kΩ
Voltage Feedback Ratio 电压反馈系数	h_{re}	$V_{CE}=-10V_{dc}, I_C=-1.0mA_{dc}, f=1.0KHz$	0.5	—	8.0	×10
Small-Signal Current Gain 小信号电流增益	h_{fe}	$V_{CE}=-10V_{dc}, I_C=-1.0mA_{dc}, f=1.0KHz$	100	—	400	—
Output Admittance输出导纳	* h_{oe}	$V_{CE}=-10V_{dc}, I_C=-1.0mA_{dc}, f=1.0KHz$	1.0	—	60	μmhos
Noise Figure噪声系数	NF	$V_{CE}=-5.0V_{dc}, I_C=-100\mu A, R_S=1.0K\Omega, f=1.0KHz$	—	—	4.0	dB

SWITCHING CHARACTERISTICS 开关特性

Delay Time 延迟时间	t_d	$V_{CC}=-3.0V_{dc}, V_{BE}=0.5V_{dc}$,	—	—	35	nS
Rise Time 上升时间	t_r	$I_C=-10mAdc, I_{B1}=-1.0mAdc$	—	—	35	
Storage Time 储存时间	t_s	$V_{CC}=-3.0V_{dc}, I_C=-10mAdc$,	—	—	225	nS
Fall Time 下降时间	t_f	$I_{B1}=I_{B2}=-1.0mAdc$	—	—	75	

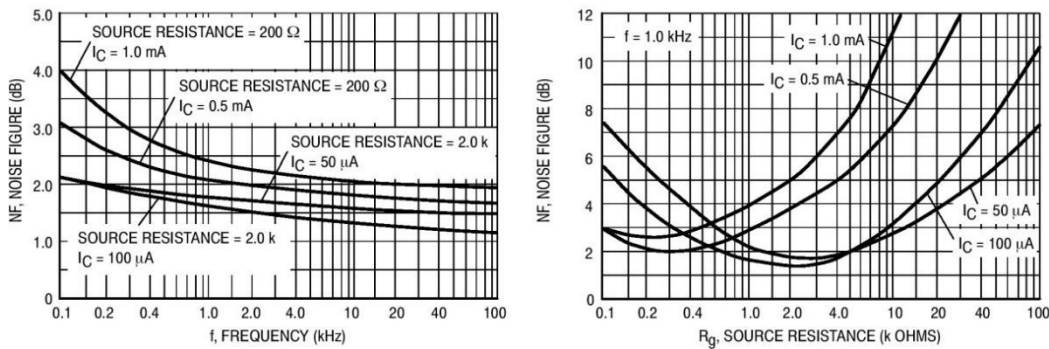
- FR-5=1.0×0.75×0.062in.
- Alumina=0.4×0.3×0.024in, 99.5%alumina.
- Pulse Width≤300μS; Duty Cycle≤2.0%.

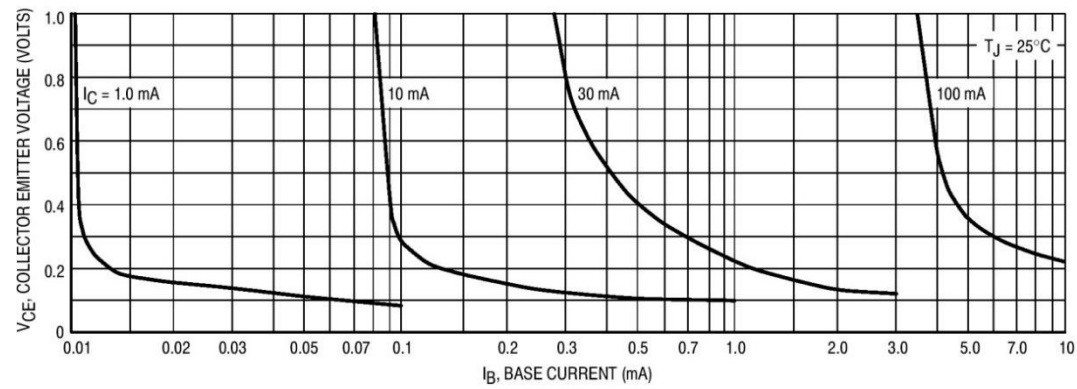
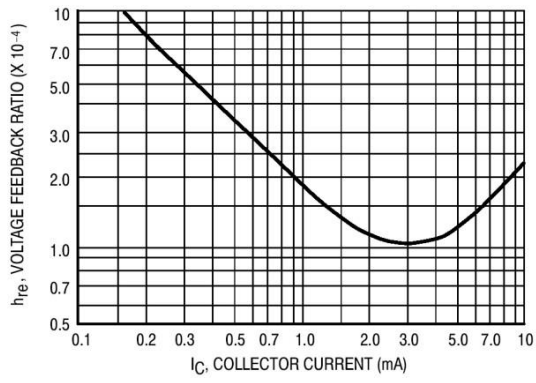
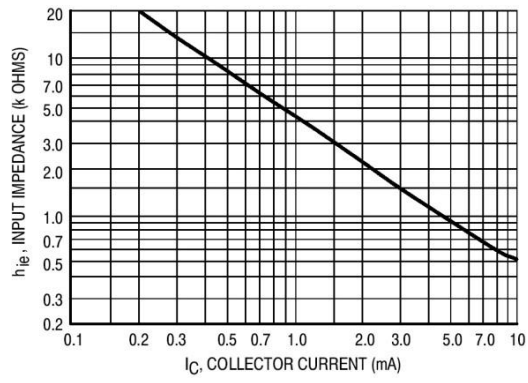
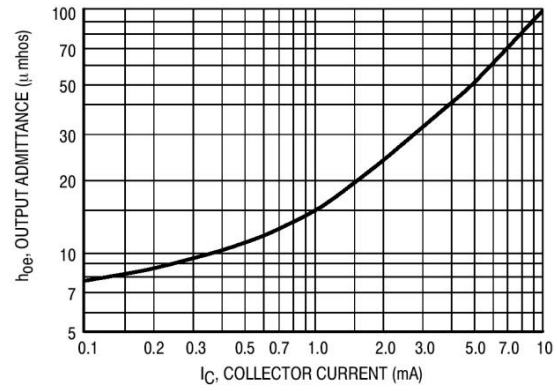
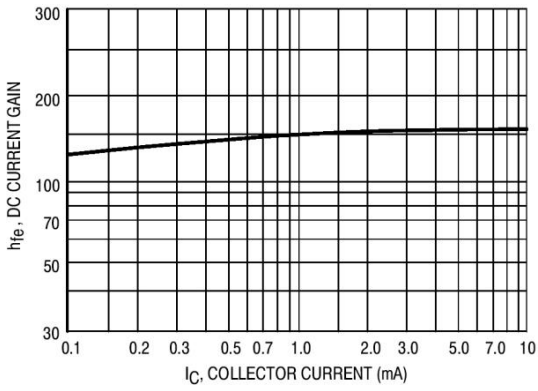
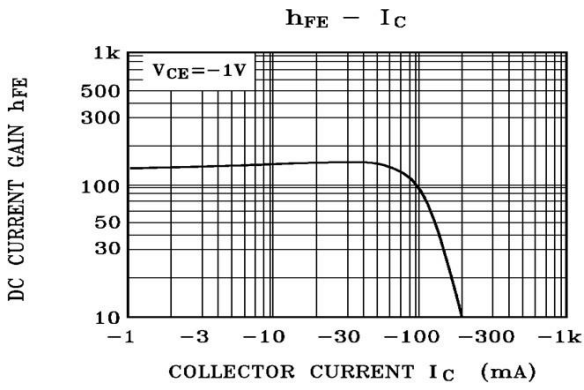
Typical Characteristics

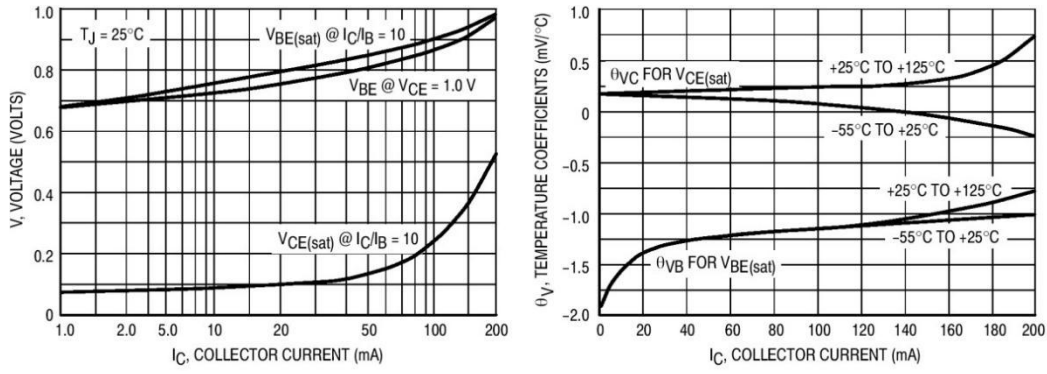


TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

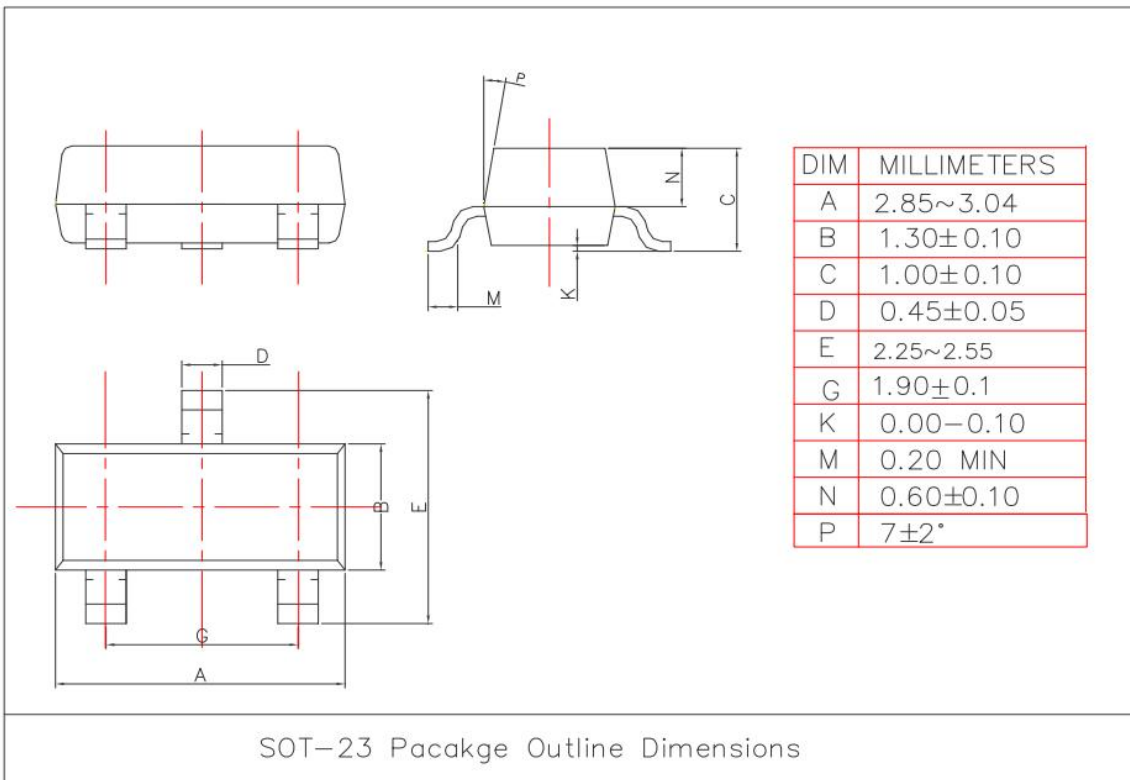
($V_{CE} = -5.0V_{dc}, T_A = 25^\circ C$, Bandwidth = 1.0 Hz)



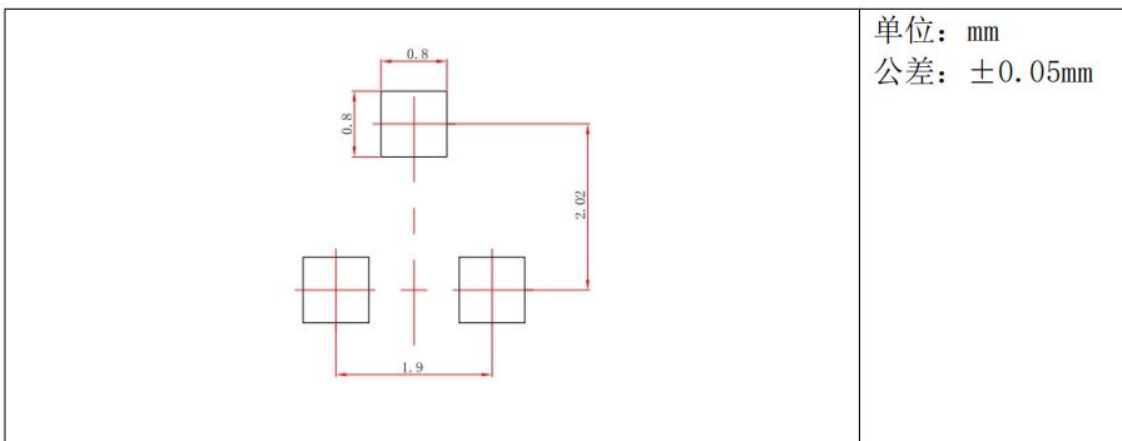




二、SOT-23 外形尺寸 (SOT-23 DIMENSION)

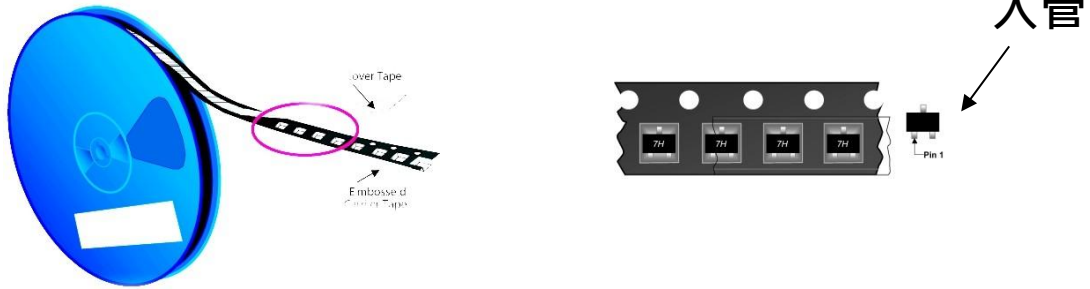


三、焊盘尺寸设计 SOT-23 Suggested Layout

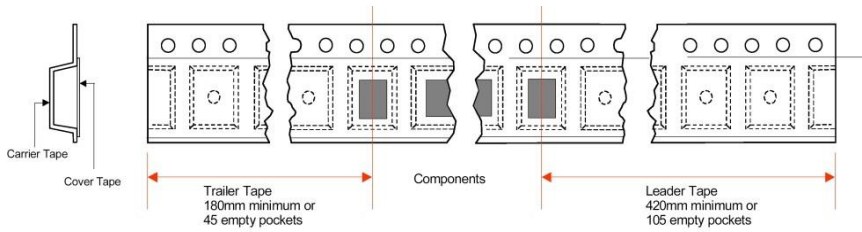


四、包装方式 Packings

封装形式	卷盘尺寸	只/卷	内盒尺寸	卷盘/内盒	只/内盒	外箱尺寸	内盒/外箱	只/外箱
SOT-23	7"	3000	190X190X135mm	10	30000	430 X 400 X 215mm	6	180K
			203X203X195mm	15	45000	440 X 440 X 230mm	4	180K



SOT-23 产品编带、包装图



SOT-23 带尾、带头空封数

